STICTION RESISTANT RELEASE PROCESS

ABSTRACT

[0036] A method of releasing a micro-electronic device formed over an insulator of a silicon-on-insulator (SOI) substrate. In one embodiment, the release method includes etching at least a portion of the insulator to separate the micro-electronic device from the SOI substrate, rinsing at least the micro-electronic device, exposing at least the micro-electronic device to a micro-sphere solution and removing the micro-electronic device from the SOI substrate. The release method may also include exposing the micro-electronic device to an etching plasma to substantially expunge the micro-sphere solution.